The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising [[resin]] polyamide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating [[film]] film;

a third insulating film provided over said drain electrode and said source electrode and comprising [[resin]] polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising [[resin]] polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film.

2. (Original) A device according to claim 1 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

3. (Original) A device according to claim 2 wherein said semiconductor film has a thickness of 100 to 750 Å.

4. (Original) A device according to claim 1 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

5. (Original) A device according to claim 1 wherein said semiconductor device is incorporated into a liquid crystal display.

6. (Original) A device according to claim 1 wherein said semiconductor device is incorporated into an electroluminescent display.

7. (Currently Amended) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising polyimide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating [[film]] film;

a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film.

8. (Original) A device according to claim 7 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

9. (Original) A device according to claim 8 wherein said semiconductor film has a thickness of 100 to 750 Å.

10. (Original) A device according to claim 7 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

11. (Original) A device according to claim 7 wherein said semiconductor device

is incorporated into a liquid crystal display.

12. (Original) A device according to claim 7 wherein said semiconductor device is incorporated into an electroluminescent display.

13. (Currently Amended) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising [[resin]] polyimide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating [[film]] film;

a third insulating film provided over said drain electrode and said source electrode and comprising [[resin]] polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising [[resin]] polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film,

wherein at least a part of said black matrix is in contact with at least a part of said one of said drain electrode and said source electrode.

14. (Original) A device according to claim 13 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

15. (Original) A device according to claim 14 wherein said semiconductor film has a thickness of 100 to 750 Å.

16. (Original) A device according to claim 13 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

17. (Original) A device according to claim 13 wherein said semiconductor device is incorporated into a liquid crystal display.

18. (Original) A device according to claim 13 wherein said semiconductor device is incorporated into an electroluminescent display.

19. (New) A semiconductor device comprising:

a channel region provided over a substrate and between a source region and a drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a first insulating film comprising silicon nitride provided over said channel region and said source region and said drain region and said gate electrode and said gate insulating film;

a second insulating film provided over said first insulating film and comprising polyamide to provide a first leveled surface over said first insulating film;

a drain electrode connected with said drain region and provided over said second insulating film;

a source electrode connected with said source region and provided over said second insulating film;

a third insulating film provided over said drain electrode and said source electrode and comprising polyimide to provide a second leveled surface over said drain electrode and said source electrode;

a black matrix provided over said third insulating film;

a fourth insulating film provided over said black matrix and comprising polyimide to provide a third leveled surface over said black matrix; and

a pixel electrode connected with one of said drain electrode and said source electrode and provided over said fourth insulating film,

wherein at least a part of said black matrix is in contact with at least a part of said one of said drain electrode and said source electrode.

20. (New) A device according to claim 19 wherein said channel region and said source region and said drain region are provided in a semiconductor film comprising a plurality of radial crystal grains of silicon.

21. (New) A device according to claim 20 wherein said semiconductor film has a thickness of 100 to 750 Å.

22. (New) A device according to claim 19 wherein said semiconductor device is incorporated into one selected from the group consisting of a portable intelligent terminal, a head mounted display, a car navigational system, a mobile telephone, a portable video camera, and a projection display.

23. (New) A device according to claim 19 wherein said semiconductor device is incorporated into a liquid crystal display.

24. (New) A device according to claim 19 wherein said semiconductor device is incorporated into an electroluminescent display.